



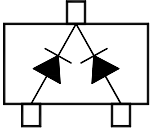
BAV70⁺ Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time

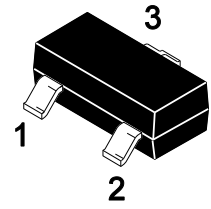
Pin Configuration

3.Cathode1、 Cathode2



1.Anode1 2.Anode2

Package



1.Anode1 2.Anode2
3.Cathode1、 Cathode2

Marking Code : A4

Electrical Characteristics (at T_J = 25°C)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V _{RRM}	100	V
Reverse Voltage	V _R	75	V
Average Rectified Forward Current	I _{F(AV)}	200	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Non-repetitive Peak Forward Surge Current	I _{FSM}	1 2	A
			at t = 1 s at t = 1 μs
Power Dissipation	P _D	350	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C



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9`YWF]WU`7\ UFUWHf]gh]Wg`fH₅1&) °CŁ

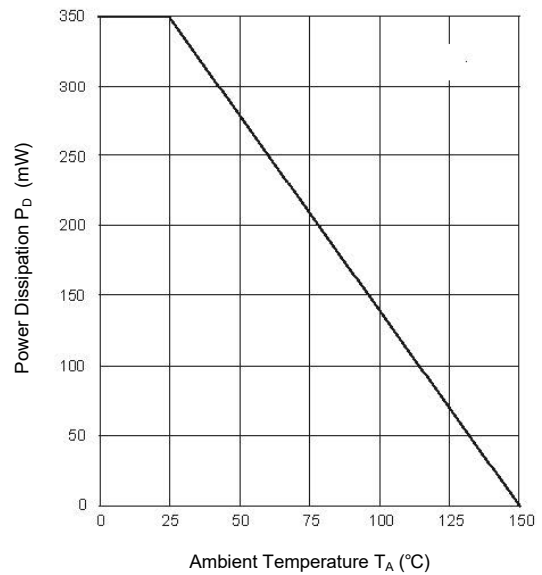
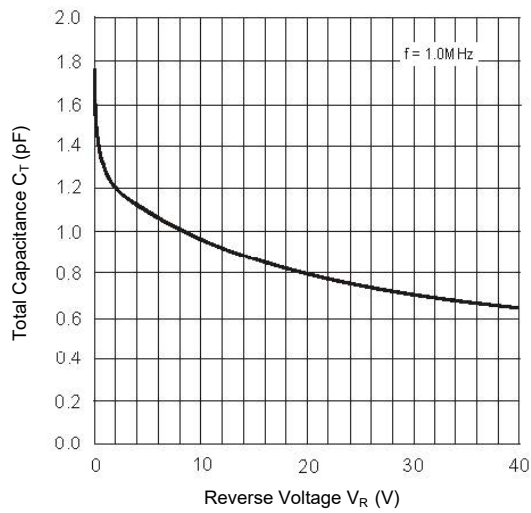
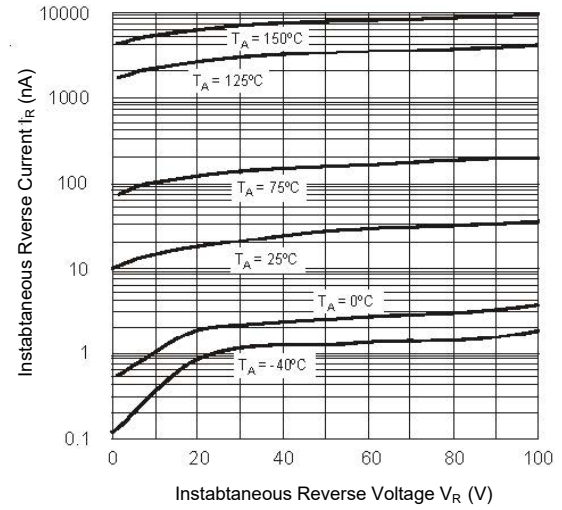
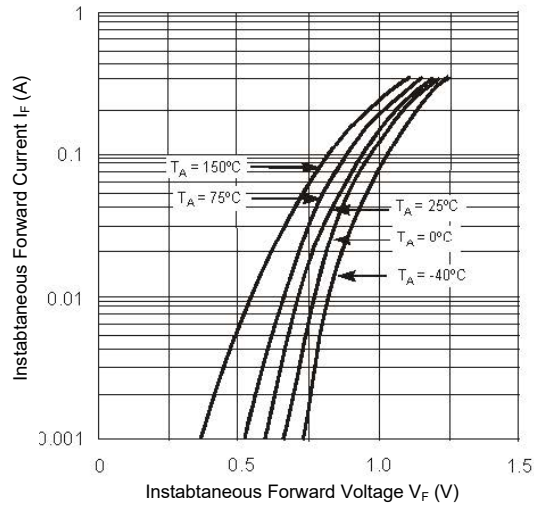
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	--	0.715 0.855 1 1.25	V
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	75	--	V
Reverse Current at $V_R = 20 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 20 \text{ V}$, at $T_J = 150 \text{ }^\circ\text{C}$ at $V_R = 75 \text{ V}$, at $T_J = 150 \text{ }^\circ\text{C}$	I_R	--	0.025 2.5 30 50	μA
Typical Junction Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_j	--	2	pF
Maximum Reverse Recovery Time at $I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $I_{RR} = 1 \text{ mA}$, $R_L = 100 \Omega$	T_{rr}	--	4	nS



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Typical Characteristic Curves





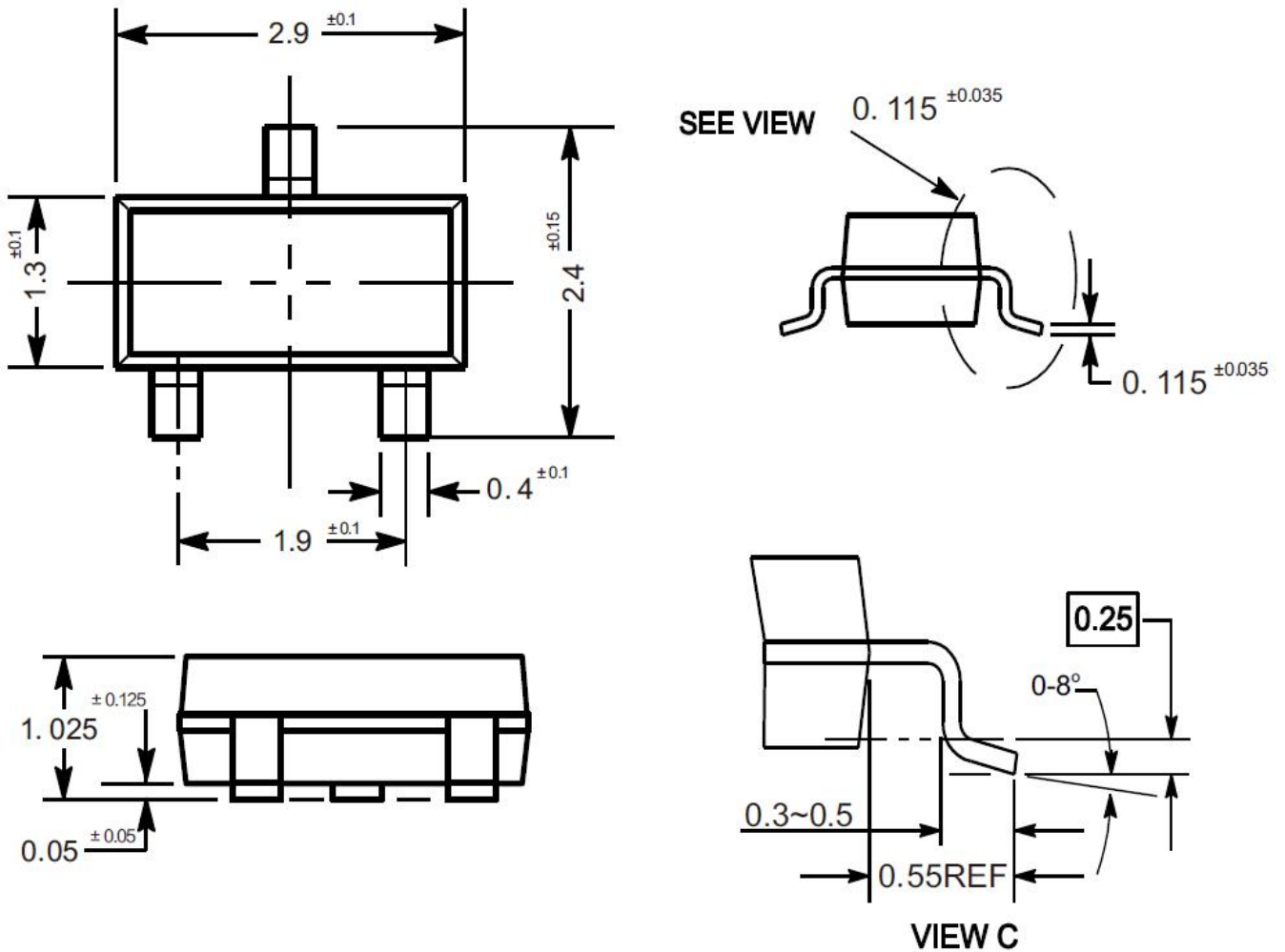
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Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
BAV70	SOT-23	3,000PCS/Reel&7inches